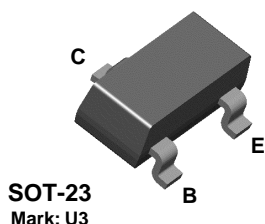


BSS64



NPN General Purpose Amplifier

This device is designed for general purpose high voltage amplifiers and gas discharge display driving. Sourced from Process 16.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	80	V
V_{CBO}	Collector-Base Voltage	120	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	200	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BSS64	
P_D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

NPN General Purpose Amplifier
(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 4.0\text{ mA}, I_B = 0$	80		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\text{ }\mu\text{A}, I_E = 0$	120		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100\text{ }\mu\text{A}, I_C = 0$	5.0		V
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 90\text{ V}, I_E = 0$ $V_{CB} = 90\text{ V}, I_E = 0, T_A = 150^\circ\text{C}$		0.1 50	μA μA
I_{EBO}	Emitter-Cutoff Current	$V_{EB} = 5.0\text{ V}, I_C = 0$		200	nA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}$	20		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 4.0\text{ mA}, I_B = 400\text{ }\mu\text{A}$ $I_C = 50\text{ mA}, I_B = 15\text{ mA}$		0.15 0.2	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 4.0\text{ mA}, I_B = 400\text{ }\mu\text{A}$		1.2	V

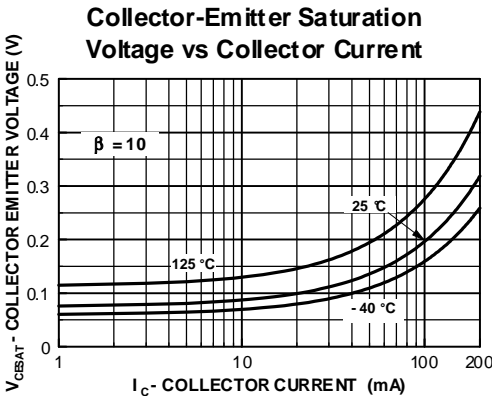
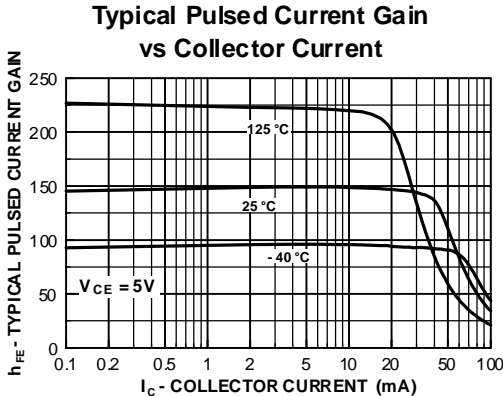
SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 4.0\text{ mA}, V_{CE} = 10,$ $f = 35\text{ MHz}$	60		MHz
C_{ob}	Output Capacitance	$V_{CB} = 10\text{ V}, f = 1.0\text{ MHz}$		5.0	pF

Spice Model

NPN (Is=2.511f Xti=3 Eg=1.11 Vaf=100 Bf=242.6 Ne=1.249 Ise=2.511f Ikf=.3458 Xtb=1.5 Br=3.197 Nc=2 Isc=0
Ikr=0 Rc=1 Cjc=4.883p Mjc=.3047 Vjc=.75 Fc=.5 Cje=18.79p Mje=.3416 Vje=.75 Tr=1.202n Tf=560p Itf=50m
Vtf=5 Xtf=8 Rb=10)

Typical Characteristics

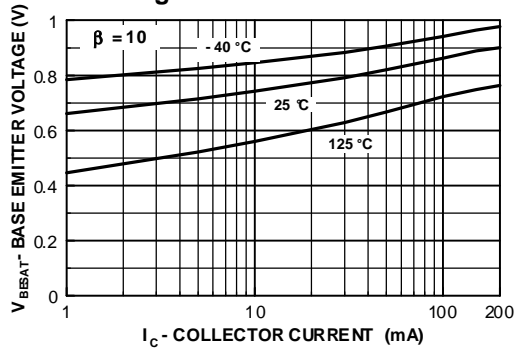


NPN General Purpose Amplifier (continued)

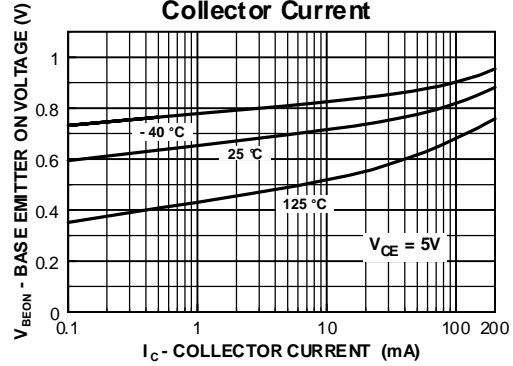
BSS64

Typical Characteristics

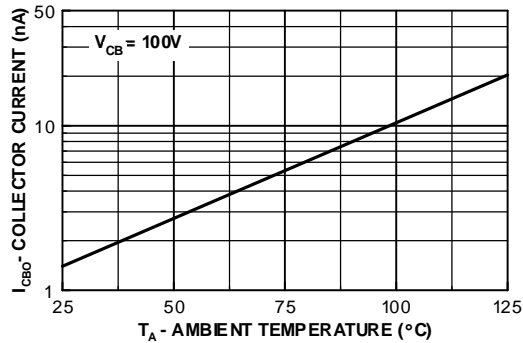
Base-Emitter Saturation
Voltage vs Collector Current



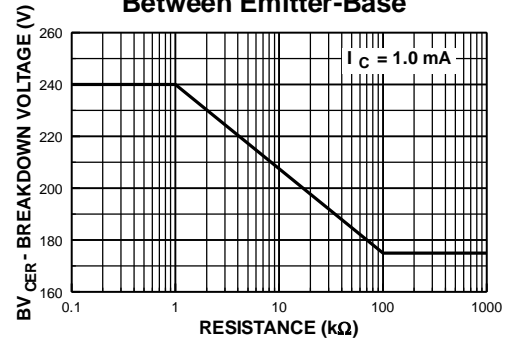
Base Emitter ON Voltage vs
Collector Current



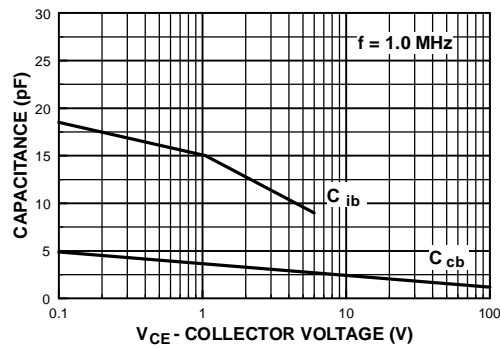
Collector-Cutoff Current
vs. Ambient Temperature



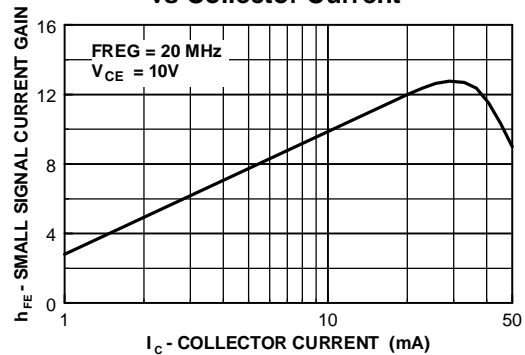
Collector-Emitter Breakdown
Voltage with Resistance
Between Emitter-Base



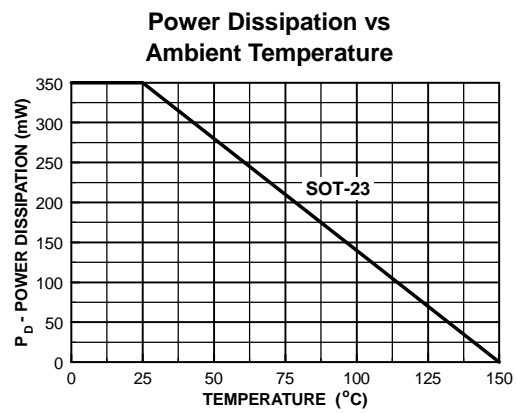
Input and Output Capacitance
vs Reverse Voltage



Small Signal Current Gain
vs Collector Current



Typical Characteristics (continued)



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DOME™	ISOPLANAR™	Quiet Series™	
E ² CMOS™	MICROWIRE™	SILENT SWITCHER®	
EnSigna™	OPTOLOGIC™	SMART START™	
FACT™	OPTOPLANAR™	SuperSOT™-3	
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PRODUCT STATUS DEFINITIONS

Definition of Terms

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.